

FAN7711 Ballast Control Integrated Circuit

Features

- Floating Channel for Bootstrap Operation to +600V
- Low Start-up and Operating Current: 120µA, 3.2mA

on

ma

- Under-Voltage Lockout with 1.8V of Hysteresis
- Adjustable Run Frequency and Preheat Time
- Internal Active ZVS Control
- Internal Protection Function (Latch Mode)
- Internal Clamping Zener Diode
- High Accuracy Oscillator
- Soft-Start Functionality

Applications

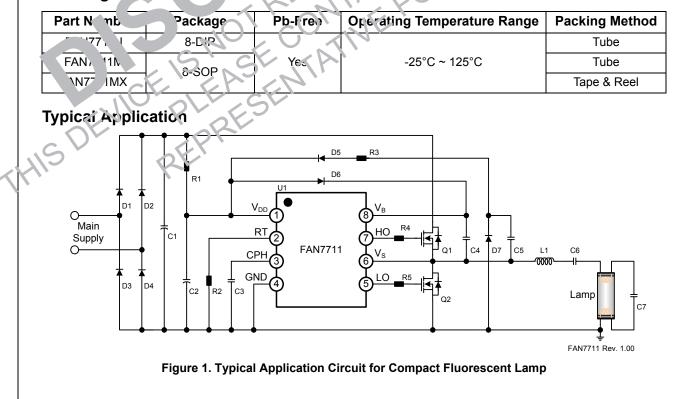
Ordering Inf

Electronic Ballast

Description

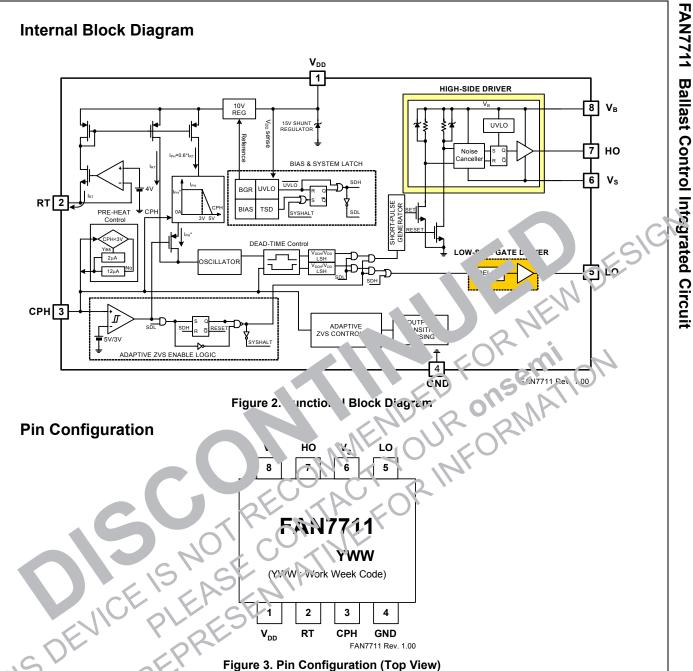
The FAN7711, developed with Fairchild's unique highvoltage process, is a ballast control integrated circuit (IC) for a fluorescent lamp. FAN7711 incorporates a preheating / ignition function, controlled by an elected external capacitor, to increase lamp life. The F. 17711 detects switch operation from a[#] igni, n mo through an internal active Zero-' age Swith in (ZVS) control circuit. This contr sci _ enable_ the FAN 711 to detect an open-lam, con, ion athout the expense of external circu. and ever strest on MOSFETs. The iver uilt in the FAN2711 has a commonhigh-side roise can alon arduit that provides robust mo high-dv/dt hoise intrusion. ายกะ วทาน.

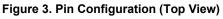




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Pin Definitions

Pin #	Name	Description	
1	V _{DD}	Supply voltage	
2	RT	Oscillator frequency set resistor	
3	CPH	Preheating time set capacitor	
4	GND	Ground	
5	LO	Low-side output	
6	V _S	High-side floating supply return	
7	НО	High-side output	
8	V _B	High-side floating supply	

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Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. T_A=25°C unless otherwise specified.

Symbol	Parameter		Min.	Тур.	Max.	Unit
VB	High-side floating supply		-0.3		625	V
Vs	High-side floating supply return		-0.3		600	V
V _{IN}	RT, CPH pins input voltage		-0.3		8	V
I _{CL}	Clamping current level				25	mA
dV _S /dt	Allowable offset voltage slew rate			51		V/ns
T _A	Operating temperature range		-25		5۲	°C
T _{STG}	Storage temperature range				50	°C
P _D	Power dissipation	8-SOP 8-E 7		0.6?5	4	w
θ_{JA}	Thermal resistance (junction-to-air)			200 100		°C/W
	CONN	T 21	JFO			
OEV	Storage temperature range Power dissipation Thermal resistance (junction-to-air) Ity a low-impedance voltage source to me vernal evice.	FON				
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Note:

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FAN7711 Ballast Control Integrated Circuit

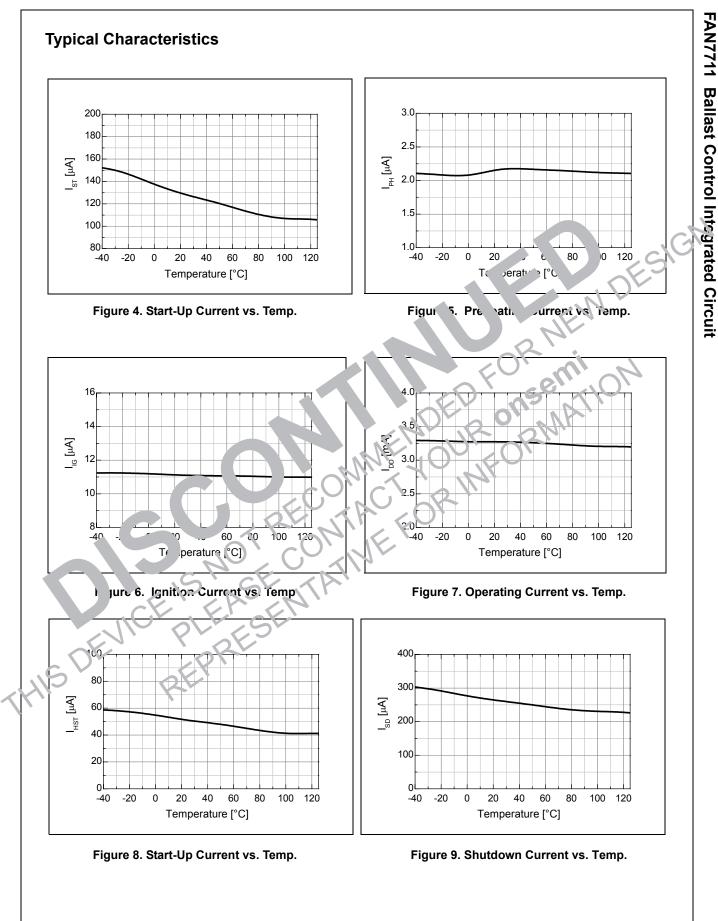
Electrical Characteristics

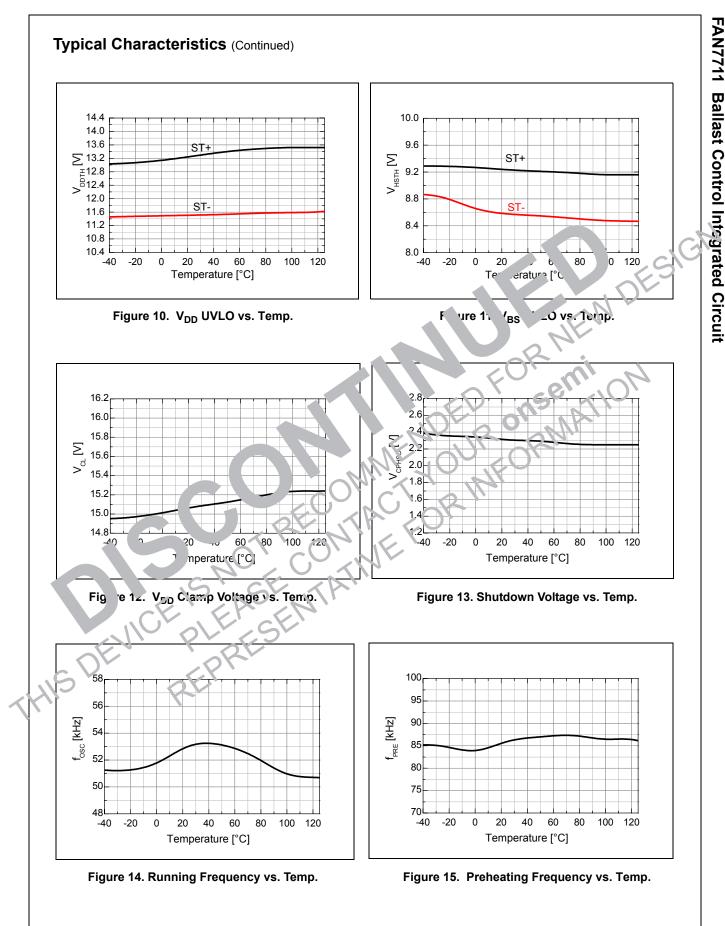
 $V_{BIAS}\,(V_{DD},\,V_{BS})$ = 14.0V, T_A = 25°C, unless otherwise specified.

Symbol	Characteristics	Conditions	Min.	Тур.	Max.	Unit
Supply Volt	tage Section			1		
V _{DDTH(ST+)}	V _{DD} UVLO positive going threshold	V _{DD} increasing	12.4	13.4	14.4	
V _{DDTH(ST-)}	V _{DD} UVLO negative going threshold	V _{DD} decreasing	10.8	11.6	12.4	1.
V _{DDHY(ST)}	V _{DD} -side UVLO hysteresis			1.8		V
V _{CL}	Supply clamping voltage	I _{DD} =10mA	14.8	15.2		1
I _{ST}	Start-up supply current	V _{DD} = 10V		120		μA
I _{DD}	Dynamic operating supply current	50kHz, C _L = 1nF		22		mA
High-Side S	Supply Section (V _B -V _S)					
V _{HSTH(ST+)}	High-side UVLO positive going threshold	V _{BS} increasing	8.5	9.2	10.0	,C
V _{HSTH(ST-)}	High-side UVLO negative going threshold	V _{BS} decreasing	.)		95	Г У
V _{HSHY(ST)}	High-side UVLO hysteresis			0.6		
I _{HST}	High-side quiescent supply current	V _{BS} = 14V		50		μA
I _{HD}	High-side dynamic operating supply current	50kHz, C _L = 1	1	NY-		mA
I _{LK}	Offset supply leakage current		7		45	μA
Oscillator S	ection)		10	7
V _{MPH}	CPH pin preheating voltage range		2.5	3.0	3.5	V
I _{PH}	CPH pin charging current during prehez g		1.25	1:.00	2.85	
I _{IG}	CPH pin charging current during	V _{CPH} = 4'	8	12	16	μA
V _{MO}	CPH pin voltage level at m			7.0		V
f _{PRE}	Preheating frequency	ר, = 80kΩ V _{CPt} = 2V	72	85	98	kHz
f _{OSC}	Running free	R _T = ευί·Ω	48.7	53.0	57.3	kHz
DT _{MAX}	Maximum c ad time	M _{CFH} = 1V, V _S = Gî∜D during preneat mode		3.1		μS
DT _{MIN}	ad time	$V_{CCH} = 6V V_S = GND$ during run mua e		1.0		μs
O. Sec	T NO CO					
I _{OH+}	h h-side driver sourcing current	PW = 10µs	250	350		[
ЭН-	High-s dc driver sinking current	PW = 10μs	500	650		
	Low-side driver sourcing current	PW = 10μs	250	350		mA
I _{OL-}	ow-side driver sink current	PW = 10µs	500	650		1
ι _{'OR}	High-side driver (ur)-on rising time	C _L = 1nF, V _{BS} = 15V		45		
	High-side driv at turn-off rising time	C _L = 1nF, V _{BS} = 15V		25		
t _{LOR}	Low-side driver turn-on rising time	C _L = 1nF, V _{BS} = 15V		45		ns
t _{LOL}	Low-side driver turn-off rising time	C _L = 1nF, V _{BS} = 15V		25		1
V _S ⁽²⁾	Maximum allowable negative V_S swing range for signal propagation to high-side output			-9.8		v
Protection (Section					
FIDIECTION	<u>۲</u>			1		
V _{CPHSD}	Shutdown voltage		2.6			V
	Shutdown voltage Shutdown current	V _{RT} = 0 after run mode	2.6	250	450	ν μA

Note:

2. This parameter, although guaranteed, is not 100% tested in production.







Typical Application Information

1. Under-Voltage Lockout (UVLO) Function

The FAN7711 has UVLO circuits for both high-side and low-side circuits. When V_{DD} reaches V_{DDTH(ST+)}, UVLO is released and the FAN7711 operates normally. At UVLO condition, FAN7711 consumes little current, noted I_{ST}. Once UVLO is released, FAN7711 operates normally until V_{DD} goes below V_{DDTH(ST-)}, the UVLO hysteresis. At UVLO condition, all latches that determine the status of the IC are reset. When the IC is in the shutdown mode, the IC can restart by lowering V_{DD} below V_{DDTH(ST-)}.

FAN7711 has a high-side gate driver circuit. The supply for the high-side driver is applied between V_B and V_S. To protect the malfunction of the driver at low supply voltage, between V_B and V_S, FAN7711 provides an additional UVLO circuit between the supply rails. If V_B-V_S is under V_{HSTH(ST+)}, the driver holds low-state to turn off the high-side switch, as shown in Figure 18. As long as V_B-V_S is higher than V_{HSTH(ST-)} after V_B-V_S exceeds V_{HSTH(ST+)}, operation of the driver continues.

2. Oscillator

The ballast circuit for a fluorescent lamp is based in the LCC resonant tank and a half-bridge investigation of the shaft-bridge investigation of the solution of the solutio

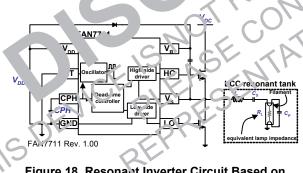


Figure 18. Resonant Inverter Circuit Based on LCC Resonant Tank

The transfer function of LCC resonant tank is heavily dependent on the lamp impedance, R_L , as illustrated in Figure 19. The oscillator in FAN7711 generates effective driving frequencies to assist lamp ignition and improve lamp life longevity. Accordingly, the oscillation frequency is changed in the following sequence:

Preheating freq.->Ignition freq.-> Normal running freq.

Before the lamp is ignited, the lamp impedance is very high. Once the lamp is turned on, the lamp impedance significantly decreases. Since the resonant peak is very high due to the high-resistance of the lamp at the instant of turning on the lamp, the lamp must be driven at higher frequency than the resonant frequency, shown as (A) in Figure 19. In this mode, the current supplied by the inverter mainly flows through C_{P} . C_{P} connects both filaments and makes the current path to ground. As a result, the current warms up the filament for easy ignition. The amount of the current can be adjusted by controlling the oscillation frequency in changing the capacitance of C_{P} . The driving inquency f_{PRE} , is called preheating frequency and inderive by:

(EQ 1)

fte. ... rm-up, the FAN7711 decreases the nue v, snown as (B) of Figure 19. This action incluse the voltage of the range and helps the fluor cent 'amp ignite. The ignition frequency is described as a function on CPH voltage, as follows:

(EC

(EQ 2)

where V_{CPH} is the voltage of CPH capacitor.

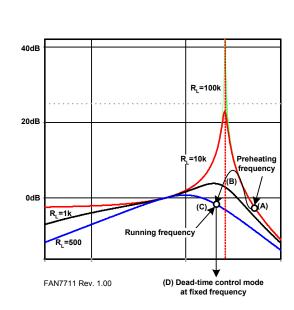
Equation 2 is valid only when V_{CPH} is between 3V to 5V before FAN7711 enters running mode. Once V_{CPH} reaches 5V, the internal latch records the exit from gnition mode. Unless V_{DD} is below $V_{DDTH(ST-)}$, the preheating and ignition modes appear only once during lamp start transition.

Finally, the lamp is driven at a fixed frequency by an external resistor, R_T , shown as (C) of Figure 19. If V_{DD} is higher than $V_{DDTH(ST+)}$ and UVLO is released, the voltage of R_T pin is regulated to 4V. This voltage adjusts the oscillator's control current according to the resistance of R_T . Because this current and an internal capacitor set the oscillation frequency, the FAN7711 does not need any external capacitors.

The proposed oscillation characteristic is given by:

$$f_{OSC} = \frac{4 \times 10^9}{RT}$$
 (EQ 3)

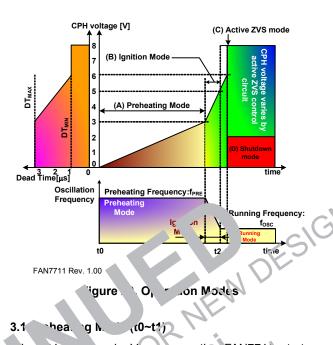
Even in the active ZVS mode, shown as (D) in Figure 19, the oscillation frequency is not changed. The dead-time is varied according to the resonant tank characteristic.





3. Operation Modes

FAN7711 has four operation modes: (A) prevating mode, (B) ignition mode, (C) active ZVS r ' ar. (D) shutdown mode, depicted in Figure 20. The new automatically selected by the volt ,e or PH spacnor, shown in Figure 20. In modes (A) nd (B), e C H actr. as a timer to determine the near grand inition times. After the preheating an ignition me ine role of the CPH is changed to s bilize 1 + active 21/3 control circuit. In this node, the last lime of the inverter is selected h th. J. of CPH. Only when FAN7711 is in active 2 mode is possible to shut of the whole sy Jun ing "Pr. Pulling the CPH pin below 2V in ive Z in de, causes the FAN7711 to enter sh. town lode. In shutdown mode, all active operation is sum a, except UVLO and some bias arcuitry. The shutdown mode is triggered by the external CPH control or the active ZVS circuit. The active ZVS circuit autoinat cally detects larip removal (open-lamp condition) and decreases CPH voltage below 2V to protect the inverter switches from damage.



her. T_{DD} eeds $V_{DDTH(ST+)}$, the FAN7711 starts op atic. At this time, an interval current source (I_{PH}) char, is CPH. CPH voltage increases non-ov to 3V in preheating mode. Accordingly, the oscillation frequency rollow, the Equation 4. In this mode, the lamp is not ignited but warmed up for easy ignition. The preheating time depends on the size of CPH:

$$= \frac{3 \times CPH}{I_{PH}}$$
 [Sec.] (EQ 4)

According to preheating process, the voltage across the lamp to ignite is reduced and the lifetime of the lamp is increased. In this mode, the dead time is fixed at its maximum value.

3.2 Ignition Mode (t1~t2)

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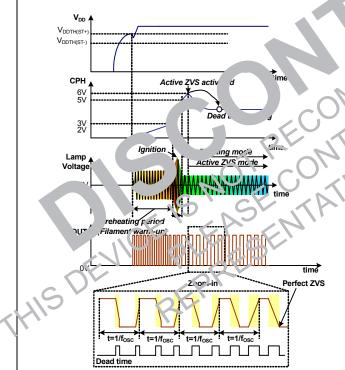
When the CPH voltage exceeds 3V, the internal current source to charge CPH is increased about six times larger than I_{PH} , noted as I_{IG} causing rapid increase in CPH voltage. The internal oscillator decreases the oscillation frequency from f_{PRE} to f_{OSC} as CPH voltage increases. As depicted in Figure 20, lowering the frequency increases the voltage across the lamp. Finally, the lamp ignites. Ignition mode is defined when CPH voltage lies between 3V and 5V. Once CPH voltage reaches 5V, the FAN7711 does not return to ignition mode, even if the CPH voltage is in that range, until the FAN7711 restarts from below $V_{DDTH(ST-)}$. Since the ignition time is given by:

$$t_{ignition} = \frac{2 \times CPH}{I_{IG}}$$
 [Sec.] (EQ 5)

In this mode, dead time varies according to the CPH voltage.

3.3 Running and Active Zero-Voltage Switching (AZVS) Modes (t2~)

When CPH voltage exceeds 5V, the operating frequency is fixed to f_{OSC} by R_T. However, active ZVS operation is not activated until CPH reaches ~6V. The FAN7711 prepares for active ZVS operation from the instant CPH exceeds 5V during t2 to t3. When CPH becomes higher than ~6V at t3, the active ZVS operation is activated. To determine the switching condition, FAN7711 detects the transition time of the output (V_S pin) of the inverter by using VB pin. From the output-transition information, FAN7711 controls the dead time to meet the ZVS condition. If ZVS is satisfied, the FAN7711 slightly increases the CPH voltage to reduce the dead time and to find optimal dead time, which increases the efficiency and decreases the thermal dissipation and EMI of the inverter switches. If ZVS fails, the FAN7711 decreases CPH voltage to increase the dead time. CPH voltage is adjusted to meet optimal ZVS operation. During the active ZVS mode, the amount of the charging/ discharging current is the same as IPH. Figure 21 depicts normal operation waveforms.

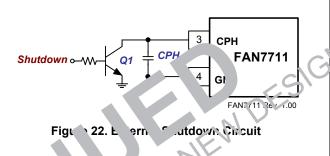


FAN7711 Rev. 1.00

Figure 21. Typical Transient Waveform from Preheating to Active ZVS Mode

3.4 Shutdown Mode

If the voltage of capacitor CPH is decreased below ~2.6V by an external application circuit or internal protection circuit, the IC enters shutdown mode. Once the IC enters shutdown mode, this status continues until an internal latch is reset by decreasing V_{DD} below V_{DDTH(ST-)}. Figure 22 shows an example of external shutdown control circuit.



The the orth charging current is the same as i, i king tossible to shut off the IC using small sig all ansistor FAN7711 orbitides active ZVS ope, ion by controlling the color of time according to the voltage of CP14. If ZVS fails even at the maximum dead ume, FAN7711 stops driving the inverter.

The FAN7711 thermal shudown circuit senses the lanction emperature of the IC. If the temperature exceeds $\sim 160^{\circ}$ C, the thermal shutdown circuit stops operation of the FAN7711.

The curren usages of shutdown mode and undervoltage lockout status are different. In shutdown mode, some circuit blocks, such as bias circuits, are kept alive. Therefore, the current consumption is slightly higher than during under-voltage lockout.

4. Automatic Open-Lamp Detection

FAN7711 can automatically detect the open-lamp condition. When the lamp is opened, the resonant tank fails to make a closed-loop to the ground, as shown in Figure 23. The supplied current from the V_S pin is used to charge and discharge the charge pump capacitor, C_P . Since the open-lamp condition means resonant tank absence, it is impossible to meet ZVS condition. In this condition, the power dissipation of the FAN7711, due to capacitive load drive, is estimated as:

$$P_{Dissipation} = \frac{1}{2} \times C_P \times V_{DC}^2 \times f \quad [W] \qquad (EQ 6)$$

where f is driving frequency and V_{DC} is DC-link voltage.

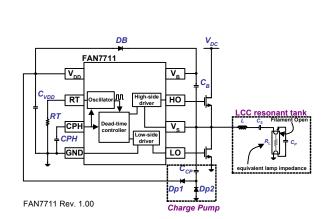


Figure 23. Current Flow When the Lamp is Open

Assuming that $C_{P_r} V_{DC}$, and f are 1nF, 311V, and 50kHz, respectively; the power dissipation reaches about 2.4W and the temperature of FAN7711 is increased rapidly. If no protection is provided, the IC can be damaged by the thermal attack. Note that hard-switching condition during the capacitive-load drive causes lots of EMI.

Figure 24 illustrates the waveforms during the operator lamp condition. In this condition, the charging and discharging current of C_P is directly determined by FAN7711 and considered hard-switching containing to the FAN7711 tries to meet ZVS condition by the FAN7711 tries to meet ZVS condition tries to meet ZVS condition by the FAN7711 tries to meet ZVS condition tries to meet ZVS condition

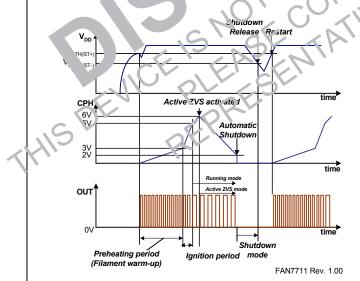
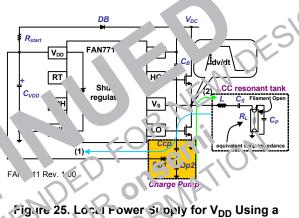


Figure 24. CPH Voltage Variation in Open-Lamp Condition

5. Power Supply

When V_{DD} is lower than $V_{DDTH(ST+)}$, it consumes very little current, I_{ST} , making it possible to supply current to the V_{DD} pin using a resistor with high resistance (R_{start} in Figure 25). Once UVLO is released, the current consumption is increased and whole circuits are operated, which requires additional power supply for stable operation. The supply must deliver at least several mA. A charge pump circuit is a cost-effective method to create an additional power supply and allows C_P to be used to reduce the EMI.



Charge Pump Circuit

As presented in Figure 25, when V_S is high, the inductor current and C_{CP} create an output transition with the slope of tv/ct. The rising edge of V_S charges C_{CP}. At that time, the current that flows through C_{CP} is:

$$I \cong C_{CP} \times \frac{dv}{dt}$$
 (EQ 7)

This current flows along the path (1). It charges C_{VDD} , which is a bypass capacitor to reduce the noise on the supply rail. If C_{VDD} is charged over the threshold voltage of the internal shunt regulator, the shunt regulator is turned on and regulates V_{DD} with the trigger voltage.

When V_S is changing from high to low state, C_{CP} is discharged through Dp2, shown as path (2) in Figure 26. These charging/discharging operations are continued until FAN7711 is halted by shutdown operation. The charging current, I, must be large enough to supply the operating current of FAN7711.

The supply for the high-side gate driver is provided by the boot-strap technique, as illustrated in Figure 26. When the low-side MOSFET connected between V_S and GND pins is turned on, the charging current for V_B flows through D_B . Every low V_S gives the chance to charge the C_B . Therefore C_B voltage builds up only when FAN7711 operates normally.

When V_S goes high, the diode D_B is reverse-biased and C_B supplies the current to the high-side driver. At this time, since C_B discharges, V_B - V_S voltage decreases. If $V_{B}\text{-}V_{S}$ goes below $V_{HSTH(ST\text{-})}\text{,}$ the high-side driver cannot operate due to the high-side UVLO protection circuit. C_B must be chosen to be large enough not to fall into UVLO range due to the discharge during a half of the oscillation period, especially when the high-side MOSFET is turned on.

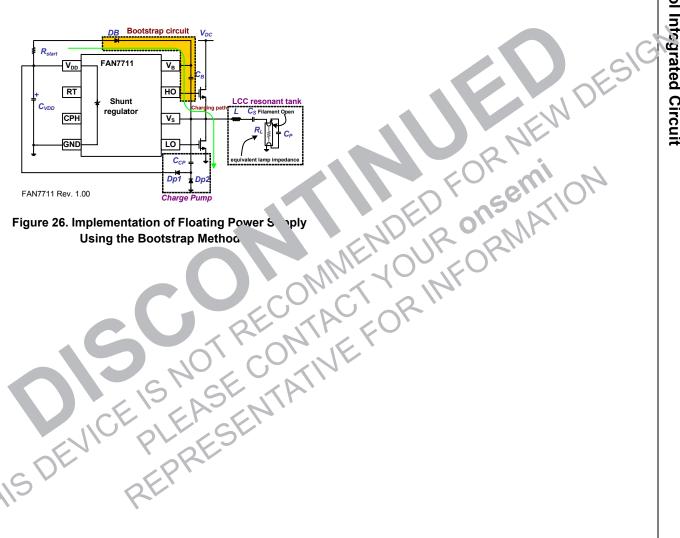


Figure 26. Implementation of Floating Power S Using the Bootstrap Method

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Design Guide

1. Start-up Circuit

The start-up current (I_{ST}) is supplied to the IC through the start-up resistor, R_{start} . Once operation starts, the power is supplied by the charge pump circuit. To reduce the power dissipation in R_{start} , select R_{start} as high as possible, considering the current requirements at startup. For 220V_{AC} power, the rectified voltage by the fullwave rectifier makes DC voltage, as shown in Equation 8. The voltage contains lots of AC component due to poor regulation characteristic of the simple full-wave rectifier:

$$V_{DC} = \sqrt{2} \times 220[V] \cong 311[V]$$
 (EQ 8)

Considering the selected parameters, $\mathsf{R}_{\text{start}}$ must satisfy the following equation:

$$\frac{V_{DC} - V_{DDTH(ST+)}}{R_{start}} > I_{ST}$$
(EQ 9)

From Equation 9, R_{start} is selected as:

$$\frac{V_{DC} - V_{DDTH(ST+)}}{I_{ST}} > R_{start}$$
(EC)

Note that if choosing the maximum R_{start} takes ong time for V_{DD} to reach $V_{DDTH(st+)}$. Considering V_{DD} g time, R_{start} must be selected as shown in the run 30.

Another important concerner to posing R_{start} is the available power rating R_{start} . To the commerciality available, low-central resistor R_{start} must obey the following rule:

 $\frac{(V_{DC} - V_{1})}{V_{SCart}} < \frac{1}{4} \cdot [V_{1}]$

A uming V_{DC} =311V and V_{CL} =15V, the minimum resume of R_{start} is about 35 JkΩ.

When the IC operates in shutdown mode due to thermal protection, open-lamp protection, or hard-switching protection, the IC consumes shutdown current, I_{SD} , which is larger than I_{ST} To prevent restart during this mode, R_{start} must be selected to cover I_{SD} current consumption. The following equation must be satisfied:

$$\frac{V_{DC} - V_{DDTH(ST+)}}{I_{SD}} > R_{start}$$
(EQ 12)

From Equations 10 - 12; it is possible to select R_{start}:

(1) For safe start-up without restart in shutdown mode:

$$4\left(V_{DC} - V_{CL}\right)^2 < R_{start} < \frac{V_{DC} - V_{DDTH(ST+)}}{I_{SD}}$$
 (EQ 13)

(2) For safe start-up with restart from shutdown mode:

$$\frac{V_{DC} - V_{DDTH(ST+)}}{I_{SD}} < R_{start} < \frac{V_{DC} - V_{DDTH(ST+)}}{I_{ST}}$$
(EQ 14)

If R_{start} meets Equation 14, restart operation is possible. However, it is not recommended to choose R_{start} at that range because V_{DD} rising time could be long and it increases the lamp's turn-on delay time, as depicted in Figure 27.

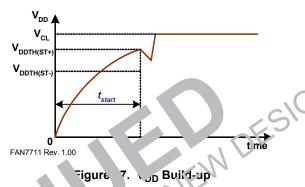


Figure 28 how the equivalent circuit for estimating that circuit analysis, M_{DD} variation versus time in tive by:

$$V_{DD}(t) = (V_{DC} - R_{start} \cdot I_{ST}) \left(e^{-t/(R_{start} C_{VDL})} \right)$$
(EQ 15)

where C_{1DD} is the total capacitance of the bypass capacitors connected between v_{DD} and GND.

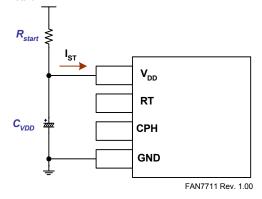
From Equation 15, it is possible to calculate t_{start} by substituting $V_{DD(t)}$ with $V_{DDTH(ST+)}$:

$$= -R_{st_{st}} \cdot C_{VDD} \cdot \ln \frac{V_{DC} - R_{start} \cdot I_{ST} - V_{DDTH(ST+)}}{V_{DD} - R_{start} \cdot I_{ST}} \quad (EQ \ 16)$$

In general, Equation 16 can be simplified as:

$$t_{start} \approx \frac{R_{start} \cdot C_{VDD} \cdot V_{DDTH(ST+)}}{V_{DC} - R_{start} \cdot I_{ST} - V_{DDTH(ST+)}}$$
(EQ 17)

Accordingly, t_{start} can be controlled by adjusting the value of R_{start} and C_{VDD}. For example, if V_{DC}=311V, R_{start}=560k, C_{VDD}=10 μ F, I_{st}=120 μ A, and V_{DDTH(ST+)}= 13.5V, t_{start} is about 0.33s.





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2. Current Supplied by Charge Pump

For the IC supply, the charge pump method is used in Figure 29. Since C_{CP} is connected to the half-bridge output, the supplied current by C_{CP} to the IC is determined by the output voltage of the half-bridge.

When the half-bridge output shows rising slope, C_{CP} is charged and the charging current is supplied to the IC. The current can be estimated as:

$$I = C_{CP} \frac{dV}{dt} \approx C_{CP} \frac{V_{DC}}{DT}$$
(EQ 18)

where DT is the dead time and dV/dt is the voltage variation of the half-bridge output.

When the half-bridge shows falling slope, C_{CP} is discharged through Dp2. Total supplied current, I_{total} , to the IC during switching period, t, is:

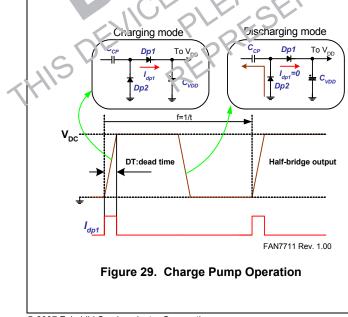
$$I_{total} = I \cdot DT = C_{CP} \cdot V_{DC}$$
(EQ 19)

From Equation 19, the average current, I_{avg} , supplied to the IC is obtained by:

$$I_{avg} = \frac{I_{total}}{t} = \frac{C_{CP} \cdot V_{DC}}{t} = C_{CP} \cdot V_{DC} \cdot f$$

For the stable operation, I multiple behic er than inerequired current. If I_{avg} is ceeds the final distribution of the shunt regulator implemented is the chip while can cause unwanted heat generation. Fore, $C_{C^{rr}}$ must be selected considering 'able oper tion and thermal generation.

f rexar, 'e, , `_{CP}=0.5nf. V_{DC}=311V, a, d f=50kHz, i_{avg} is ₹.8mA t is enough current for stable operation.



3. Lamp Turn-on Time

The turn-on time of the lamp is determined by supply build-up time t_{start} , preheating time, and ignition time; where t_{start} has been obtained by Equation 17. When the IC's supply voltage exceeds $V_{DDTH(ST+)}$ after turn-on or restart, the IC operates in preheating mode. This operation continues until CPH pin's voltage reaches ~3V. In this mode, CPH capacitor is charged by I_{PH} current, as depicted in Figure 30. The preheating time is achieved by calculating:

$$t_{preheat} = 3 \frac{CPH}{I_{PF}}$$
 (EQ 2'

The preheating time is elled to it ip life (especially filament); therefore, he that stics of a given lamp should be co. idered her, bosing the lime.

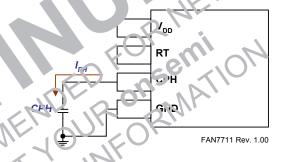


Figure 30. Preheating Timer

Compared to the preheating time, it is almost impossible to exactly predict the ignition time, whose definition is the time from the end of the preheating time to ignition. In general, the lamp ignites during the ignition mode. Therefore, assume that the maximum ignition time is the same as the duration of ignition mode, from 3V until CPH reaches 5V. Thus, ignition time can be defined as:

$$t_{ignition} = (5-3)\frac{CPH}{I_{IG}} = 2\frac{CPH}{I_{IG}}$$
(EQ 22)

Note that, at ignition mode, CPH is charged by I_{IG} , which is six times larger than I_{PH} . Consequently, total turn-on time is approximately:

VDD Build-Time + Preheating Time + Ignition Time =

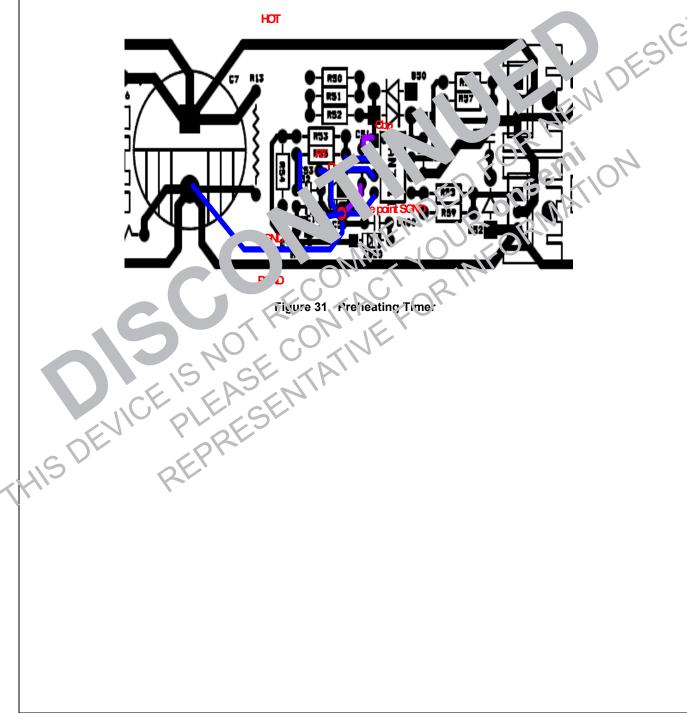
$$t_{ignition} = (5-3)\frac{CPH}{I_{IG}} = 2\frac{CPH}{I_{IG}} \text{ [Sec.]}$$
 (EQ 23)

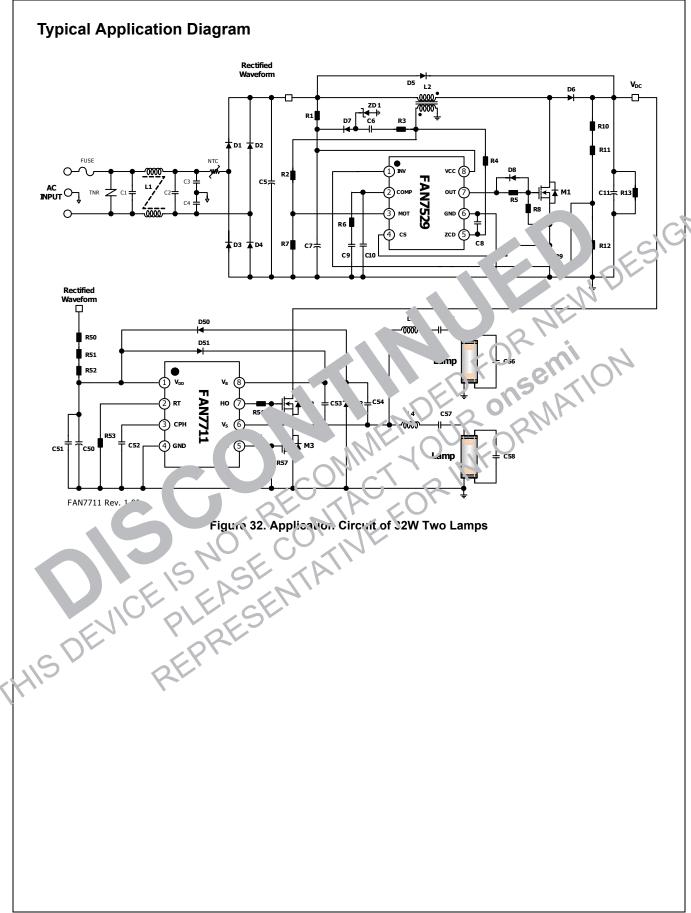
4. PCB Guideline

Component selection and placement on PCB is important when using power control ICs. Bypass the V_{CC} to GND as close to the IC terminals as possible with a low-ESR/ESL capacitor, as shown in Figure 31. This bypassed capacitor (C_{BP}) can reduce the noise from the power supply parts, such as start-up resistor and charge pump.

The signal GND must be separated from the power GND. So, the signal GND should be directly connected to the rectify capacitor using an individual PCB trace.

In addition, the ground return path of the timing components (C_{PH} , R_T) and V_{DD} decoupling capacitor should be connected directly to the IC GND lead and not via separate traces or jumpers to other ground traces on the board. These connection techniques prevent high-current ground loops from interfering with sensitive timing component operations and allow the control circuit to reduce common-mode noise due to output switching.



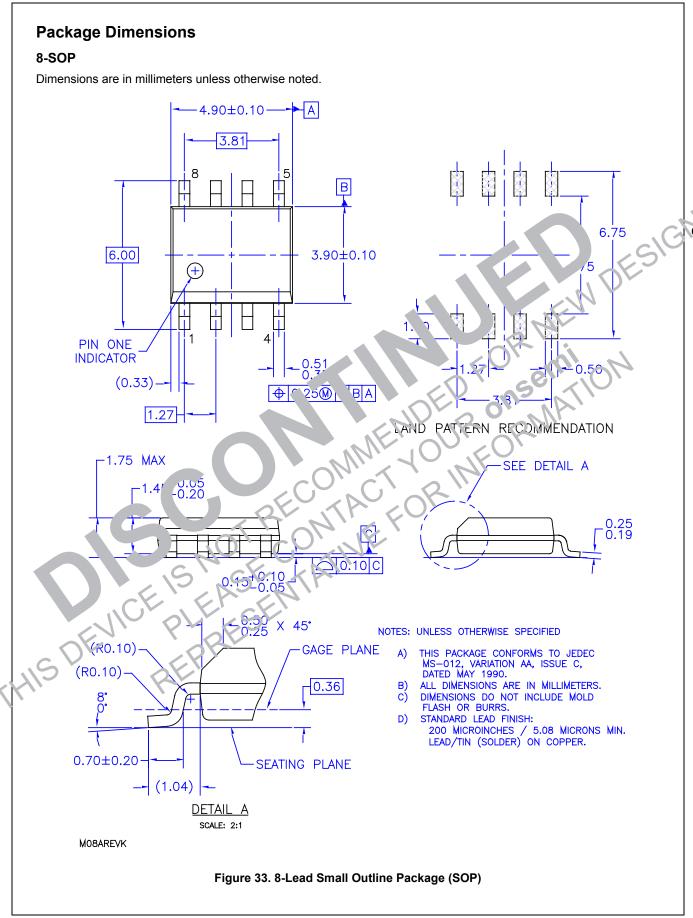


Part	Value	Note	Part	Value	Note
	Resistor		C55	15nF/630V	Miller Capacitor
R1	330kΩ	1/2W	C56	2.7nF/1kV	Miller Capacitor
R2	750kΩ	1/4W	C57	15nF/630V	Miller Capacitor
R3	100Ω	1/2W	C58	2.7nF/1kV	Miller Capacitor
R4	20k Ω	1/4W		Diode)
R5	47Ω	1/4W	D1	1N4007	1kV,1A
R6	10kΩ	1/4W	D2	1N4007	1kV,1A
R7	50k Ω	1/4W	D3	1N4007	1kV,1A
R8	47 kΩ	1/4W	D4	1N4007	, /,1A
R9	0.3Ω	1W	D5	UF400-	trp ast,1kV.1A
R10	1MΩ	1/4W	D6	UF 707	Unra Fast, 1kV,1A
R11	1MΩ	1/4W	D7	1N41, 7	100V,1A
R12	12.6kΩ	1/4W,1%	D8	N414	100V,1A
R13	220k Ω	2W	D.	Ur-1007	Ultra Fast,1kV,1A
R50	150kΩ	1/4W	51	UF4007	じたo Fast.11.1.1A
R51	150kΩ	1/4W		'JF-1007	Ultra Fast.1. V,1A
R52	150kΩ	1/4W	ZD1	IN4746A	Zener 18V, 1W
R53	90kΩ	1/ ~		MOSF	- Nr
R54	10Ω	1/4 7	Mil	FOP.F5N60C	500V,6A
R55	47Ω	40	M2	FQPF5N50C	500V,5A
R56	47kΩ	./4W	i/J3	FQPF5N50C	500V,5A
R57	47 Ω	1/.1\/		Fuse	
R58	47kQ	1/4W	Fuse	3A/250V	
	apacit	0		TNR	
Т	47	Eux Capacitor	TNR	471	
C2	າ J∂nF/275V _{AC}	вох Сарасі, ог			
3	2206pF/3kV	Cerarnic Capacitor		NTC	
C4	2200pF/3kV	Cerariic Capacitor	NTC	10D-09	
C5	0.22µF/630V	Miller Capacitor		Line Fil	ter
CG	12nF/50`√	Ceramic Capacitor	LF1	40mH	
C7	22µF/50₩	Electrolytic Capacitor		Transfor	mer
C8	39pF/50V	Ceramic Capacitor	L1	0.94mH(75T:10T)	EI2820
C9	1µF/50V	Ceramic Capacitor		Inducto	or
C10	0.1µF/50V	Ceramic Capacitor	L2	3.2mH(130T)	EI2820
C11	47µF/450V	Electrolytic Capacitor	L3	3.2mH(130T)	EI2820
C50	10µF/50V	Electrolytic Capacitor		IC	
C51	1µF/50V	Ceramic Capacitor	U1	FAN7711	Fairchild Semiconductor
C52	0.47µF/25V	Ceramic Capacitor,5%	U2	FAN7529	Fairchild Semiconductor
C53	100nF/50V	Ceramic Capacitor			
C54	470pF/1kV	Ceramic Capacitor			

FAN7711 Ballast Control Integrated Circuit

Component List for 20W CFL

Part	Value	Note	Part	Value	Note	
Resistor		Diode				
R1	470kΩ	1/4W	D1	1N4007	1kV/1A	
R2	90kΩ	1/4W	D2	1N4007	1kV/1A	
R3	10Ω	1/4W	D3	1N4007	1kV/1A	
R4	47Ω	1/4W	D4	1N4007	1kV/1A	
R5	47Ω	1/4W	D5	UF4007	1kV/1A,Ultra Fast	
			D6	UF4007	1	
	Capaci	tor	D7	UF4007	1kV/i Ultra Fast	
C1	22µF/250V	Electrolytic Capacitor		lr .ct	tor	
C2	10µF/50V	Electrolytic Capacitor	L1	2.5m ^L ' (28)	E16.6S	
C3	470nF/25V	Miller Capacitor		<u> </u>	F	
C4	100nF/25V	Miller Capacitor	Q1	F PF1N, C	500V,1A	
C5	470pF/630V	Miller Capacitor	C		500V,1A	
C6	33nF/630V	Miller Capacitor	<u> </u>	IC IC	4	
C7 lote: . Refer to	3.3nF/1kV the typical applicatio	Miller Capacito	MEN	EANITRI DE OF	I sinchild Semiconduct	
lote:	the typical applicatio		MER	PEAN7711	I zirchild Semicone	



Package Dimensions 8-DIP Dimensions are in inches and [millimeters] unless otherwise noted. .400 10.15 .373 9.46 Α $\langle c \rangle$.036 [0.9 TYP] (.092) [Ø2.337] (.032) [R0.813] PIN #1 .250±.005 [6.35±0.13] PIN #1 $\langle \mathbb{C} \rangle$ DESI \sim в 1 4 רסף עיי א אר יי TOP VIEW **OPTION 1** .070 1.78 .045 1.14 210±.01 7.87⊾ .130±.005 3±0. $\langle D \rangle$ 21 AM 5.33] Ċ .015 N IN [0.38] .021 0.53 .015 0.37 .300 140 73.55 [7.62] ⊕ .001[.02^F _J] C 6. .100 430 MAX [2.541 [10.92] .060 MAX E. JV1 [1.52] CONFORMS TO JEDEC RECISTRATION MS-001 .010+.005 0.254+0.127 VARIATIONS BA S. CONTROLING D'MENSIONS AFE IN MICHES REFERENCE D'MENSIONS AFE IN MILLIMETERS CDUES NOT INCLUDE MOLD TASH OR PROTRUSIONS. MOLD FLASH OR PROTI USIONS SHALL NOT EXCEED .010 INCHES OP. J.2. MM. DOES NOT INCLUDE DAMBAR PROTRUSIONS. DAMBAR PROFINUSIONS SHALL NOT EXCEED .010 INCHES OR 0.25MM. E. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994. N08EREVG Figure 34. 8-Lead Dual In-Line Package (DIP)

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